

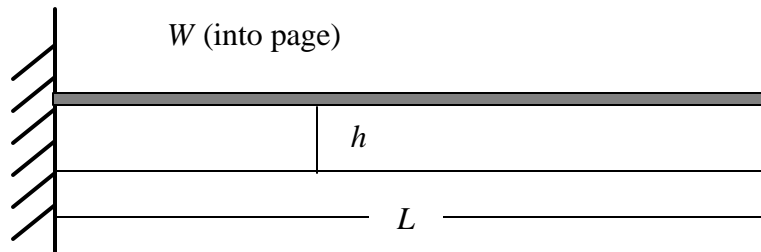
UNIVERSITY OF CALIFORNIA AT BERKELEY
College of Engineering
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Problem Set #3 Solutions

EECS C245 / ME C218

Fall 2003

1. A 100 nm-thick film of low-stress (silicon rich) silicon nitride is deposited on the top surface of a single crystal silicon cantilever having dimensions $L = 1$ cm, $W = 1$ mm, and $h = 200$ μm . The film is deposited at 835 $^{\circ}\text{C}$ by LPCVD. The longitudinal axis of the cantilever is aligned with the $\langle 100 \rangle$ axis of the silicon crystal.



- a) At room temperature, the residual stress in the silicon nitride film is σ_r . Considering the silicon cantilever to be constrained (zero deflection) at this point, find an expression for the built-in bending moment M_z .
- b) When the cantilever is released, find an expression for the tip deflection at the end of the cantilever.
- c) If the tip deflection is 1 μm , find the numerical value of the residual stress at room temperature, the thermal stress at room temperature, and the intrinsic stress. Use the material properties given in Table 8.1 of *Microsystem Design*.

$$M_z \approx \int_{-h/2}^{h/2+t} W z' \sigma(z') dz' \approx \frac{h}{2} W t \sigma_r$$

$$y(L) = \frac{M_z}{2EI_y} L^2 = \frac{\frac{h}{2} W t \sigma_r L^2}{2 \left(\frac{1}{12}\right) h^2 (\tilde{E}_{Si} h + 3\tilde{E}_n t) W}$$

$$\tilde{E}_{Si} = \frac{E_{100}}{1-\nu_{100}} = 180 \text{ GPa} \quad \leftarrow \text{error in Eq. (9.94)}$$

$$\tilde{E}_n = \frac{E_n}{1-\nu_n} = \frac{270 \text{ GPa}}{1-0.27} = 370 \text{ GPa}$$

$$\sigma_r = \left(\frac{20}{6L^2 t}\right) h (\tilde{E}_{Si} h + 3\tilde{E}_n t) \approx \frac{2\tilde{E}_{Si} h^2 \Delta}{6L^2 t} = 240 \text{ MPa}$$

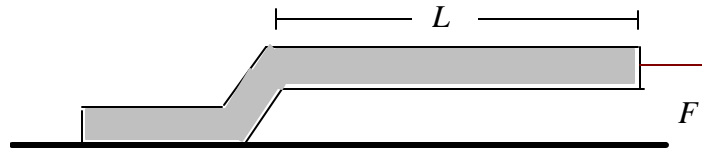
$L = 200 \mu\text{m}$ $t = 0.1 \mu\text{m}$

$$\sigma_T = \tilde{E}_n \Delta \alpha \Delta T = (370 \text{ GPa})(2.3-2.8) \times 10^{-6} \text{ K}^{-1} (835-25) \text{ K}$$

$$= -150 \text{ MPa}$$

$$\sigma_{\text{int}} = \sigma_r - \sigma_{Tn} = 380 \text{ MPa}$$

2. Axially loaded beams are useful for designing high stiffness springs. The polysilicon beam below is 4 μm wide and 2 μm thick. The beam is suspended 1 μm above the substrate. You can consider that the anchor is perfectly clamped.



- Find the length L of this beam needed to obtain a spring constant $k_x = 250 \mu\text{N}/\mu\text{m}$.
- Find the spring constant of this beam in the y and z directions using first-order linear beam mechanics.
- The “step-up” anchor does not clamp the beam perfectly. Estimate the x -axis spring constant for this beam by considering the step as a very stubby beam. If you’re so inclined, you can try to include the effect of shear.

$$a) \quad \epsilon_x = \frac{x}{L} = \frac{\sigma}{E} = \frac{F_x}{EhW} \Rightarrow F_x/x = k_x = \frac{EhW}{L}$$

$$L = \frac{EhW}{k_x} = 5.1 \text{ mm} \dots \text{too long!}$$

$$b) \quad k_y = \frac{EhW^3}{4L^3} = 3.8 \times 10^{-5} \mu\text{N}/\mu\text{m}$$

$$k_z = \frac{EWh^3}{4L^3} = 9.5 \times 10^{-6} \mu\text{N}/\mu\text{m}$$

c) Simple analysis of anchor (

$$k'_x = \frac{Eh^3W^3}{4L'^3} \approx 1.3 \times 10^6 \mu\text{N}/\mu\text{m}$$

$$k_x^{-1} = k_x^{-1} + k_{x'}^{-1} \approx k_x$$

small

3. In Lecture 7, there is an SEM of the ADXL-05’s folded suspension. You are asked by a new startup called Lightweight Xcell, Inc. (not a Berkeley spin-off) to see how a copy of this structure would perform if it was made out of sputtered aluminum, rather than polysilicon. The Lightweight CTO has an answer to your immediate reaction that Al is a lousy MEMS material: the ADXL-05 is a closed-loop accelerometer and so the Al suspension won’t move ... much, anyway. The folded suspension has 2 μm -wide and thick beams, with the long leg being 150 μm long and the short leg 130 μm long. The area of the shuttle with comb fingers is 44,000 μm^2 .

- If the aluminum is stress free at room temperature, what is the spring constant along the sensitive axis in N/m?
- Redesign the folded suspension so that the spring constant is the same as for the polysilicon ADXL-05’s.
- The product has to work over a temperature range of -25°C to 125°C . Estimate the spring constant at the temperature extremes of the aluminum xcell; you need consider only the effects of thermal stress.
- Would you invest in Lightweight?

③ a) $k_{\text{guided}} = \frac{EWh^3}{L^3}$ $E_{\text{Al}} = 70 \text{ GPa}$

short leg $k_1 = \frac{(70 \text{ GPa})(2 \mu\text{m})(2 \mu\text{m})^3}{(130 \mu\text{m})^3} = 0.51 \text{ N/m}$

long leg $k_2 = \frac{(70 \text{ GPa})(2 \mu\text{m})(2 \mu\text{m})^3}{(150 \mu\text{m})^3} = 0.33 \text{ N/m}$

Overall: $k = 4 \left(\frac{1}{k_1^{-1} + k_2^{-1}} \right) = \frac{4(0.51)(0.33)}{0.51 + 0.33} = 0.8 \mu\text{N}/\mu\text{m}$

b) Easy way is to scale the beam thickness h (in the direction of bending - "linewidth") to increase k_{AC} to $k_{\text{poly-Si}}$:

$k_{\text{poly}} = \frac{E_{\text{Si}}}{E_{\text{Al}}} k_{\text{AC}} = \left(\frac{160}{170} \right) (0.8 \text{ N/m}) = 1.3 \text{ N/m}$

$\therefore (h'/2 \mu\text{m})^3 = 1.6/0.8 \Rightarrow h' = \sqrt[3]{\frac{1.6}{0.8}} 2 \mu\text{m} = 2.8 \mu\text{m}$

c) flawed problem! I'd intended you to find the locked-in thermal strain

$\epsilon_r \left(\frac{L_s}{L} \right) \dots$ with $L_s \sim 15 \mu\text{m}$.

full credit for this.

then find S in the two legs, find $k_1(S)$, $k_2(S)$ and get the overall $k(T)$. Some found that the long leg buckled at $T = 125^\circ\text{C}$. In any case, $L_s \approx 1 \mu\text{m}$ for the $\chi L = 0.5 \Rightarrow k \approx \text{constant}$ (w/ except for $E_{\text{Al}}(T)$)



d) risk isn't $k(T)$, it's the difficulty in controlling $\bar{\sigma}_r$ and T in Al films.

Please post your questions on our newsgroup: ucb.class.ee245